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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Satoshi TAKEI et al.

Application No.: 10/544,129

Group Art Unit: 2812

Filed: August 2, 2005

Docket No.: 124936

For: ACRYLIC POLYMER-CONTAINING GAP FILL MATERIAL FORMING  
COMPOSITION FOR LITHOGRAPHY

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 8-11.
- ☒ 3. One or more reference cited herein was cited in a counterpart foreign application. An English language version of the European search report is attached for the Examiner's information. See References 1, 5-7, and 10.
- ☒ 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- ☒ 5. An English language Abstract of one or more non-English language reference is attached hereto. See References 6 and 8-11.
- ☒ 6. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and is attached, but has not been reviewed for accuracy. See References 8-10.

☒ 7. Reference 1 corresponds to reference 10.

Respectfully submitted,



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Date: June 19, 2006

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**DEPOSIT ACCOUNT USE  
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Sheet 1 of 1

Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 124936		APPLICATION NO. 10/544,129	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANT(S) Satoshi TAKEI et al.			
				FILING DATE August 2, 2005		GROUP 2812	
U.S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Name			
	1	2002/0110665 A1	8/15/2002	RUTTER, JR. et al.			
	2	5,919,599 A	7/6/1999	MEADOR et al.			
	3	5,693,691 A	12/2/1997	FLAIM et al.			
	4	6,057,239 A	5/2/2000	WANG et al.			
FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
	5	GB 1 496 345 A	12/30/1977	GREAT BRITAIN			
	6	DE 42 36 673 A1	5/5/1994	GERMANY	X		
	7	GB 939,212	10/9/1963	GREAT BRITAIN			
	8	JP 2000-294504 A	10/20/2000	JAPAN	X	X	
	9	JP 2002-190519 A	7/5/2002	JAPAN	X	X	
	10	JP 2002-047430 A	2/12/2002	JAPAN	X	X	
	11	WO 02/05035	1/17/2002	WIPO	X		
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
	12	Tom Lynch et al., "Properties and Performance of Near UV Reflectivity Control Layers," US, in Advances in Resist Technology and Processing XI, Omkaram Nalamasu ed., Proceedings of SPIE, 1994, Vol. 2195, p. 225-229;					
	13	G. Taylor et al., "Methacrylate Resist and Antireflective Coatings for 193 nm Lithography," US, in Microlithography 1999: in Advances in Resist Technology and Processing XVI, Will Conley ed., Proceedings of SPIE, 1999, Vol. 3678, p. 174-185;					
	14	Jim D. Meador et al., "Recent Progress in 193 nm Antireflective Coatings," US, in Microlithography 1999; in Advances in Resist Technology and Processing XVI, Will Conley ed., Proceedings of SPIE, 1999, Vol. 3678, p. 100-109.					
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: June 19, 2006